AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A method comprising:

patterning a plurality of signal lines from a metal material as a terminal conductive layer of an integrated circuit die;

patterning a plurality of first protective structures to surround the signal lines; and

patterning a plurality of second protective structures to surround each of the first protective structures,

wherein a first protective structure and a second protective structure surround and enclose respective ones of the plurality of signal lines.

2. (Currently Amended) The method of claim 1, further comprising:

patterning the first protective structures as a continuous structures to enclose the signal lines; and

patterning the second protective structures as a continuous structures to enclose the first protective structures.

3. (Original) The method of claim 1, further comprising:

patterning the first and second protective structures to one of a low rail supply line and a high rail supply line.

4. (Currently Amended) A method comprising:

forming a first interconnection metallization layer on a substrate;

forming a second interconnection metallization layer on the first interconnection metallization layer;

forming a plurality of [at least one] signal lines coupled to the first interconnection metallization layer in the second interconnection metallization;

forming a plurality of first protective structures that surround[s] the at least one signal line in the second interconnection metallization layer; and

forming a plurality of second protective structures that surround[s] the first protective structures,

wherein a first protective structure and a second protective structure surround and enclose respective ones of the plurality of signal lines.

5. (Currently Amended) The method of claim 4, wherein forming the first protective structures comprises using a continuous loop-like shape protective structures to enclose the signal lines; and

wherein forming the second protective structures comprises using a plurality of continuous loop-like shape protective structures to enclose the first protective structures.

6. (Previously Presented) The method of claim 4, further comprising coupling at least one of the protective structures to a low rail supply voltage.

7. (Previously Presented) The method of claim 4, further comprising coupling at least one of the protective structures to a high rail supply voltage.

8. (Currently Amended) The method of claim 4, wherein the first protective structures are [is] spaced from the signal lines at approximately 2 microns.

9. (Original) The method of claim 4, wherein the first interconnection metallization layer has a first volume and the second interconnection metallization layer has a second volume greater than the first volume.

10. (Currently Amended) The method of claim 4, wherein the forming the protective structures comprises forming a plurality of protective structures (PSi) for i = 1...N, the first protective structures PS1 surrounding the signal lines, each protective structure PSi surrounding a previous protective structure PSi-1.